NSN 5962-01-413-5397

Memory Microcircuit - Page 1 of 1



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-55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius End Application: F-16 acft Features Provided: Electrostatic sensitive and monolithic Inclosure Material: Silicon Inclosure Configuration: Leadless flat pack Output Logic Form: Complementary-metal oxide-semiconductor logic Criticality Code Justification: Cibbl Product Name: Microcircuit, memory, digital, cmos 128k x 8 bit eeprom, monolithic silicon Voltage Rating And Type Per Characteristic: -0.5 volts total supply and 6.0 volts total supply Time Rating Per Chacteristic: 120.00 nanoseconds access Memory Device Type: Eeprom Special Features: 10 ms write speed, byte/page write mode, 10,000 cycle endurance Test Data Document: 96906-mil-std883 standard (includes industry or association standards, individual manufactureer standards, etc.). Terminal Type And Quantity: 44 leadless Shelf Life: N/a Unit Of Measure:	Operating Tempurature Range:
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Shelf Life: N/a Unit Of Measure:	Terminal Type And Quantity:
N/a Unit Of Measure:	44 leadless
Unit Of Measure:	Shelf Life:
	N/a
	Unit Of Measure:
Demilitarization:	Demilitarization:
Yes - demil/mli	Yes - demil/mli
Fiig:	Fiig:
	A458a0
A459a0	M4JOdU M4JOdU